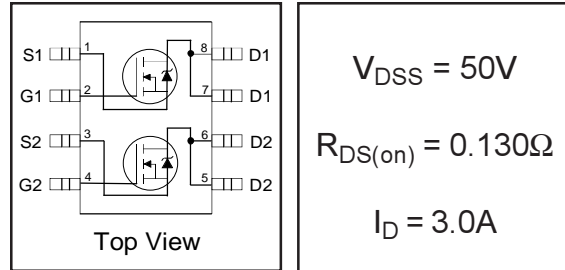


# IRF7103IPbF

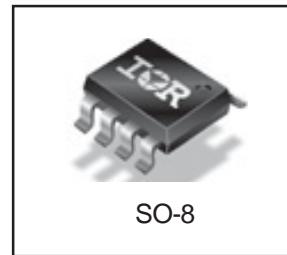
HEXFET® Power MOSFET

- Advanced Process Technology
- Ultra Low On-Resistance
- Dual N-Channel MOSFET
- Surface Mount
- Available in Tape & Reel
- Dynamic dv/dt Rating
- Fast Switching
- Lead-Free



## Description

The SO-8 has been modified through a customized leadframe for enhanced thermal characteristics and dual-die capability making it ideal in a variety of power applications. With these improvements, multiple devices can be used in an application with dramatically reduced board space. The package is designed for vapor phase, infra red, or wave soldering techniques. Power dissipation of greater than 0.8W is possible in a typical PCB mount application.



## Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	3.0	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	2.3	
$I_{DM}$	Pulsed Drain Current ①	10	
$P_D @ T_C = 25^\circ C$	Power Dissipation	2.0	W
	Linear Derating Factor	0.016	W/°C
$V_{GS}$	Gate-to-Source Voltage	$\pm 20$	V
dv/dt	Peak Diode Recovery dv/dt ②	4.5	V/nS
$T_J, T_{STG}$	Junction and Storage Temperature Range	-55 to + 150	°C

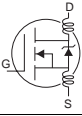
## Thermal Resistance Ratings

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JA}$	Maximum Junction-to-Ambient ④	—	—	62.5	°C/W

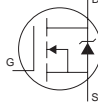
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International  
**IR** Rectifier

## Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V <sub>(BR)DSS</sub>	Drain-to-Source Breakdown Voltage	50	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
ΔV <sub>(BR)DSS/ΔT<sub>J</sub></sub>	Breakdown Voltage Temp. Coefficient	—	0.049	—	V/°C	Reference to 25°C, I <sub>D</sub> = 1mA
R <sub>DS(ON)</sub>	Static Drain-to-Source On-Resistance	—	0.11	0.13	Ω	V <sub>GS</sub> = 10V, I <sub>D</sub> = 3.0A ③
		—	0.16	0.20		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 1.5A ③
V <sub>GS(th)</sub>	Gate Threshold Voltage	1.0	—	3.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
g <sub>fs</sub>	Forward Transconductance	—	3.8	—	S	V <sub>DS</sub> = 15V, I <sub>D</sub> = 3.0A ③
I <sub>DSS</sub>	Drain-to-Source Leakage Current	—	—	2.0	μA	V <sub>DS</sub> = 40V, V <sub>GS</sub> = 0V
		—	—	25		V <sub>DS</sub> = 40V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 55 °C
I <sub>GSS</sub>	Gate-to-Source Forward Leakage	—	—	100	nA	V <sub>GS</sub> = 20V
	Gate-to-Source Reverse Leakage	—	—	-100		V <sub>GS</sub> = -20V
Q <sub>g</sub>	Total Gate Charge	—	12	30	nC	I <sub>D</sub> = 2.0A
Q <sub>gs</sub>	Gate-to-Source Charge	—	1.2	—		V <sub>DS</sub> = 25V
Q <sub>gd</sub>	Gate-to-Drain ("Miller") Charge	—	3.5	—		V <sub>GS</sub> = 10V ③
t <sub>d(on)</sub>	Turn-On Delay Time	—	9.0	20	ns	V <sub>DD</sub> = 25V
t <sub>r</sub>	Rise Time	—	8.0	20		I <sub>D</sub> = 1.0A
t <sub>d(off)</sub>	Turn-Off Delay Time	—	45	70		R <sub>G</sub> = 6.0Ω
t <sub>f</sub>	Fall Time	—	25	50		R <sub>D</sub> = 25Ω ③
L <sub>D</sub>	Internal Drain Inductance	—	4.0	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact 
L <sub>S</sub>	Internal Source Inductance	—	6.0	—		
C <sub>iss</sub>	Input Capacitance	—	290	—	pF	V <sub>GS</sub> = 0V
C <sub>oss</sub>	Output Capacitance	—	140	—		V <sub>DS</sub> = 25V
C <sub>rss</sub>	Reverse Transfer Capacitance	—	37	—		f = 1.0MHz

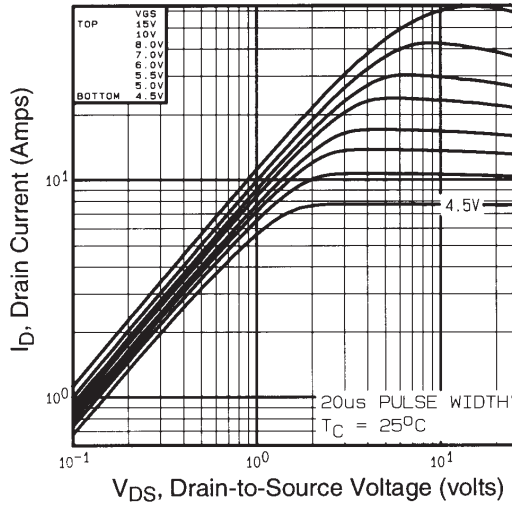
## Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	2.0	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I <sub>SM</sub>	Pulsed Source Current (Body Diode) ①	—	—	12		
V <sub>SD</sub>	Diode Forward Voltage	—	—	1.2	V	T <sub>J</sub> = 25°C, I <sub>S</sub> = 1.5A, V <sub>GS</sub> = 0V ③
t <sub>rr</sub>	Reverse Recovery Time	—	70	100	ns	T <sub>J</sub> = 25°C, I <sub>F</sub> = 1.5A
Q <sub>rr</sub>	Reverse Recovery Charge	—	110	170	nC	di/dt = 100A/μs ③
t <sub>on</sub>	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L <sub>S</sub> +L <sub>D</sub> )				

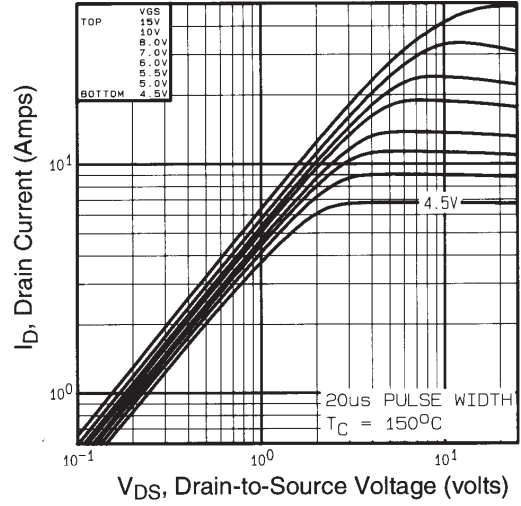
### Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.  
 ② I<sub>SD</sub> ≤ 1.8A, di/dt ≤ 90A/μs, V<sub>DD</sub> ≤ V<sub>(BR)DSS</sub>, T<sub>J</sub> ≤ 150°C

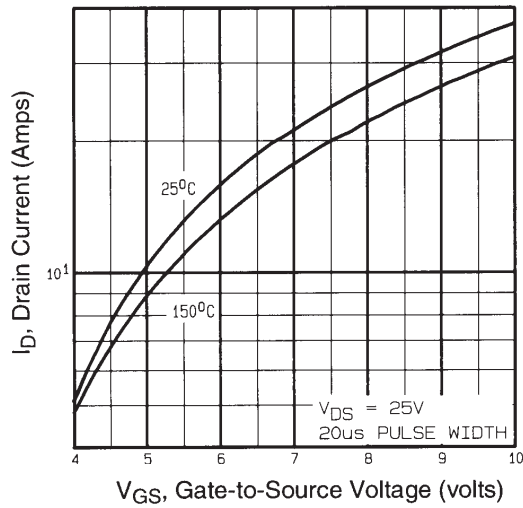
- ③ Pulse width ≤ 300μs; duty cycle ≤ 2%.  
 ④ Surface mounted on FR-4 board, t ≤ 10sec.



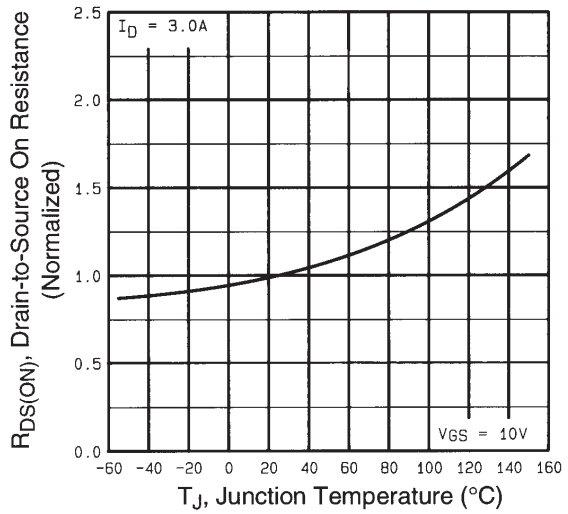
**Fig 1.** Typical Output Characteristics,



**Fig 2.** Typical Output Characteristics,

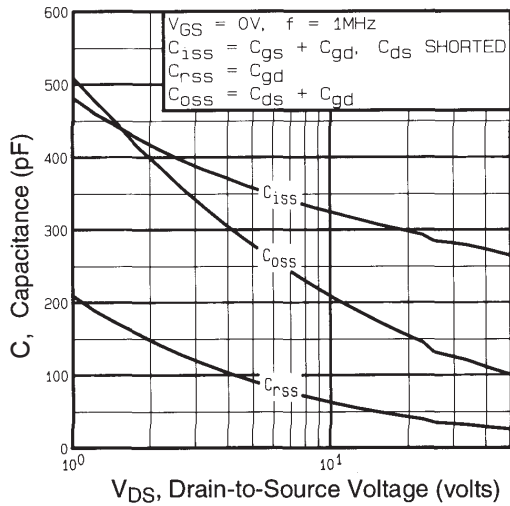


**Fig 3.** Typical Transfer Characteristics

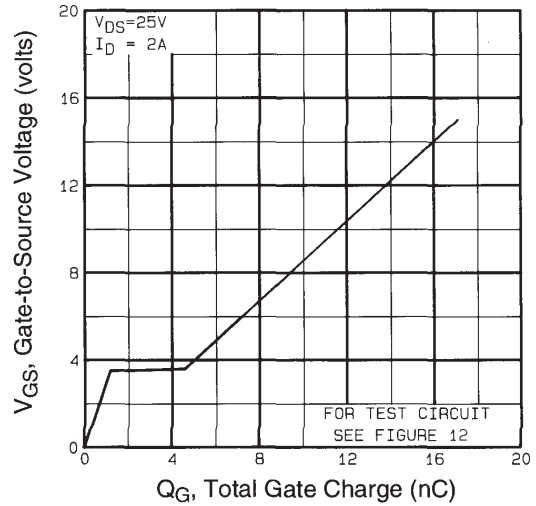


**Fig 4.** Normalized On-Resistance Vs. Temperature

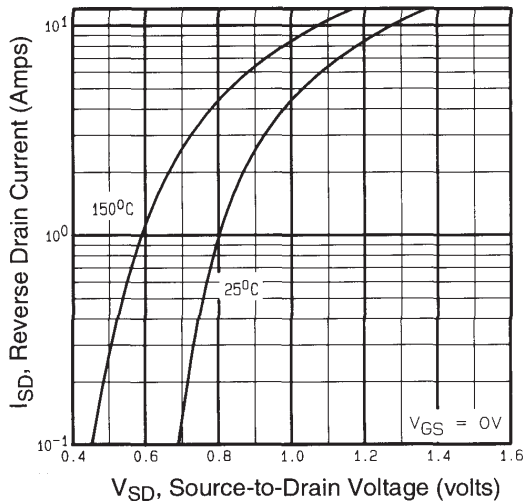
# IRF7103IPbF



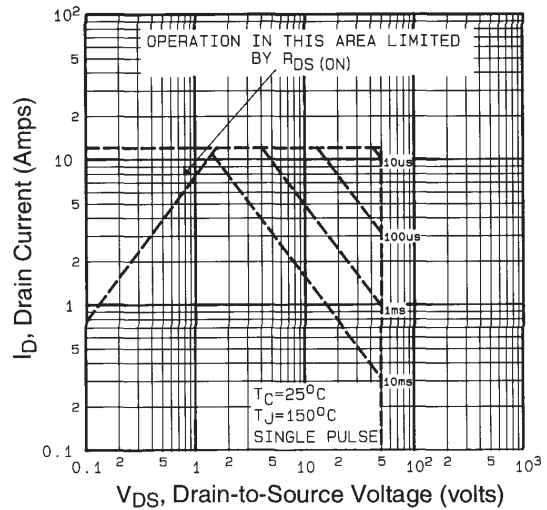
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



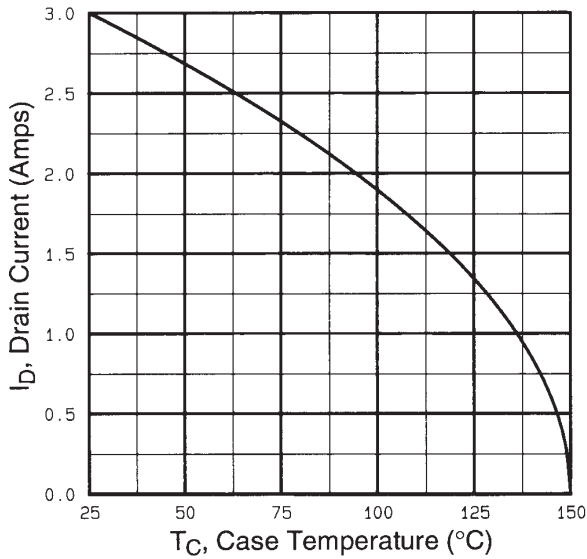
**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



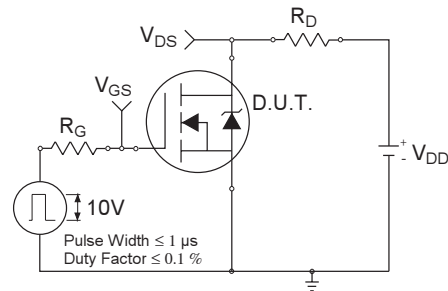
**Fig 7.** Typical Source-Drain Diode Forward Voltage



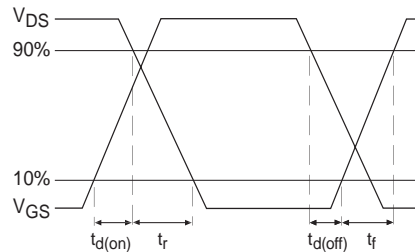
**Fig 8.** Maximum Safe Operating Area



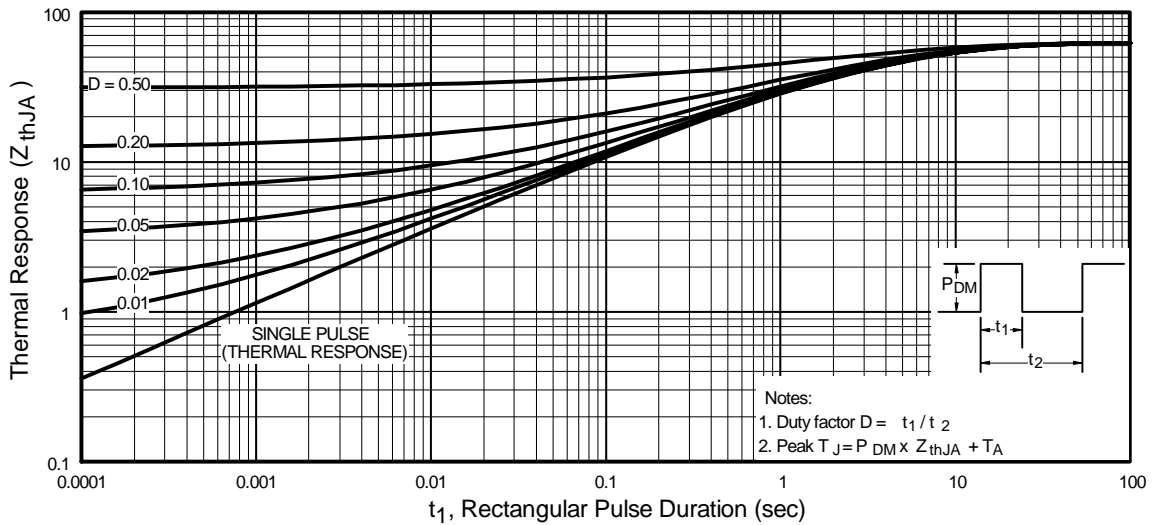
**Fig 9.** Maximum Drain Current Vs. Case Temperature



**Fig 10a.** Switching Time Test Circuit



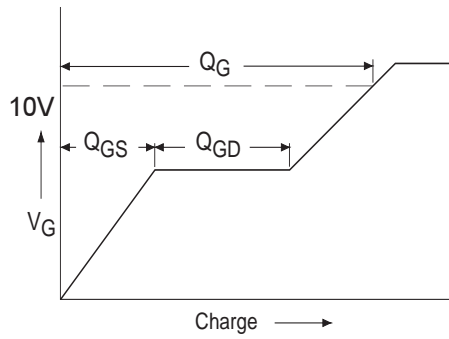
**Fig 10b.** Switching Time Waveforms



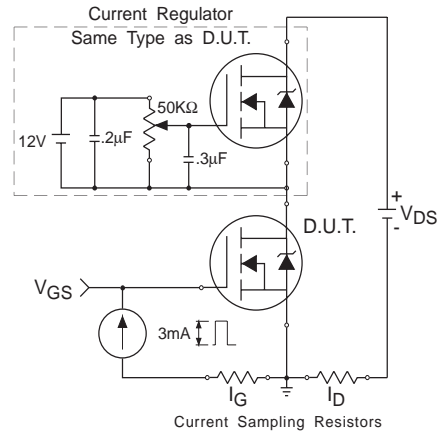
**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

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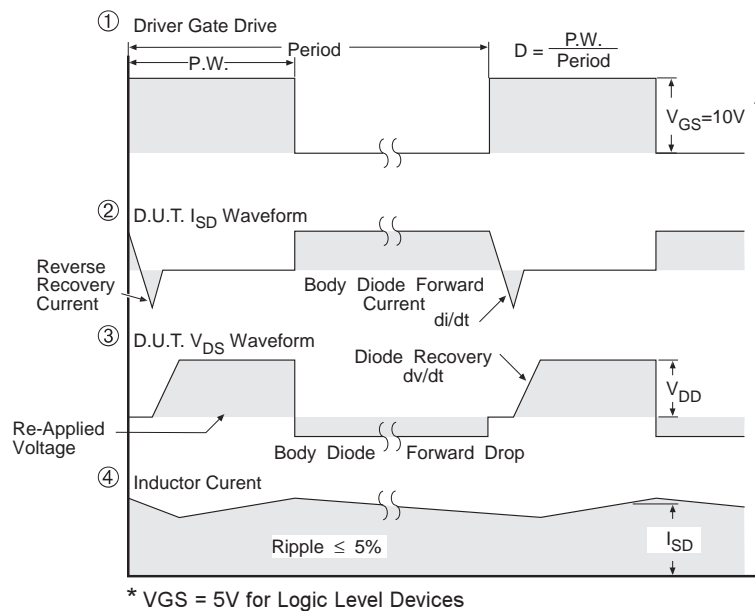
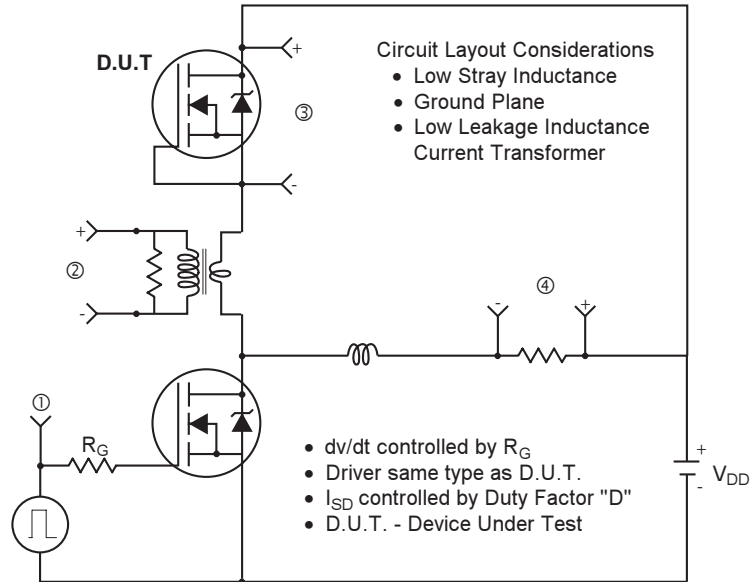


**Fig 12a.** Basic Gate Charge Waveform



**Fig 12b.** Gate Charge Test Circuit

## Peak Diode Recovery dv/dt Test Circuit

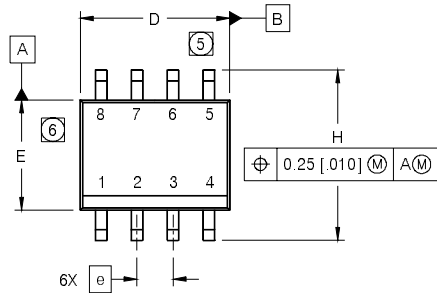


**Fig 13. For N-Channel HEXFETS**

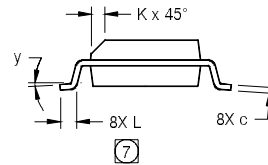
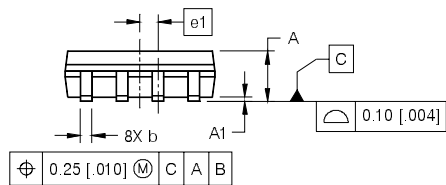
# IRF7103IPbF

## SO-8 Package Outline

Dimensions are shown in millimeters (inches)



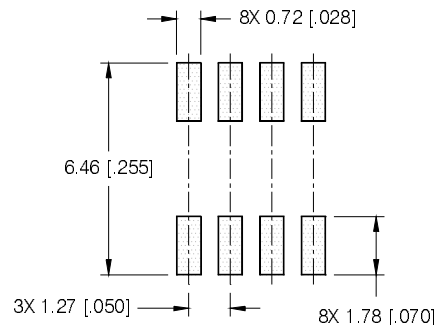
DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
y	0°	8°	0°	8°



**NOTES:**

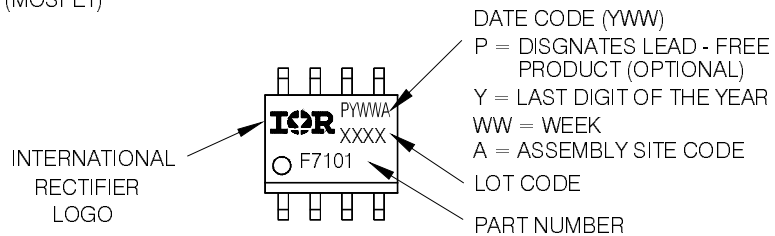
1. DIMENSIONING & TOLERANCING PER ASME Y1 4.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
- ⑤ DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 [0.006].
- ⑥ DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 [0.010].
- ⑦ DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.

**FOOTPRINT**



## SO-8 Part Marking Information

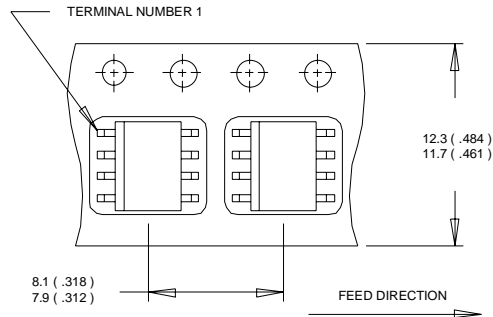
EXAMPLE: THIS IS AN IRF7101 (MOSFET)



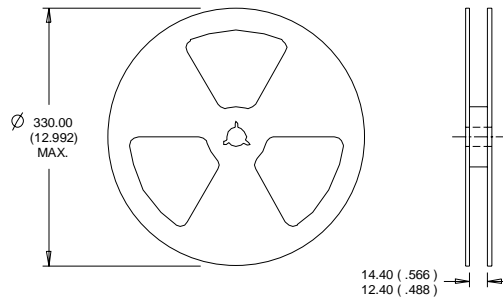


## SO-8 Tape and Reel

Dimensions are shown in millimeters (inches)



- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
  2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
  3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES :
1. CONTROLLING DIMENSION : MILLIMETER.
  2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Data and specifications subject to change without notice.  
 This product has been designed and qualified for the Industrial market.  
 Qualifications Standards can be found on IR's Web site.